

Terahertz System Integration Platforms: Metallic vs. Dielectric

Tadao Nagatsuma⁽¹⁾ and Masayuki Fujita⁽¹⁾

(1) Osaka University, e-mail: nagatuma@ee.es.osaka-u.ac.jp

Recently, there has been increasing interest in the application of terahertz (THz) waves for communications and sensing with the advance of enabling technologies for signal generation and detection, where both electronic and photonic devices are currently available [1]. One of the critical and practical issues that we face in the THz regions is a loss of RF interconnections as frequencies increase. Hollow waveguides have been conventionally employed to accommodate high-frequency devices and circuits [2]. However, RF loss is not negligibly small at frequencies above 500 GHz due to metallic loss of waveguides, and also the assembly of semiconductor devices on such waveguides becomes extremely difficult due to reduction in the size of waveguides below several hundreds of microns. Low-cost and reproducible integration/packaging technologies are urgently required to expand applications of THz systems.

In this paper, we discuss the issue of loss in interconnections in THz integrated circuits, and compare two promising solutions; MEMS-based metallic-waveguide platforms [3, 4] and dielectric-waveguide platforms [5, 6]. Figure 1 shows a schematic concept of future THz integrated systems, based on the two platforms to support the integration of functional devices. In addition, we also discuss two options, optical cables and dielectric RF cables, for inter-module connections between transmitter/receiver main frames and antenna frontends.

This work is partially supported by the Core Research for Evolutional Science and Technology (CREST) program of Japan Science and Technology Agency (#JPMJCR1534), and ONR Foreign Research Grant (N62909-18-1-2015).

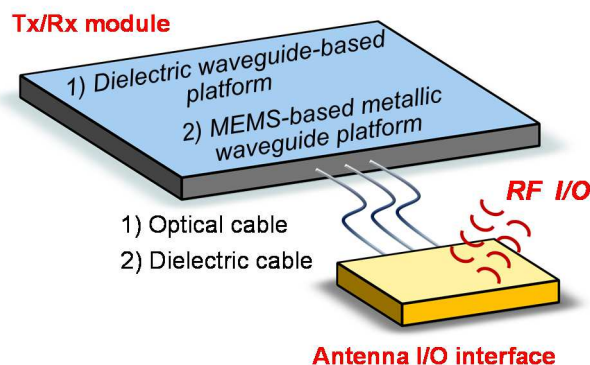


Figure 1. Concept of THz integrated electronic and photonic systems.

References

- [1] K. Sengupta *et al.*, "Terahertz Integrated Electronic and Hybrid Electronic-Photonic Systems," *Nat. Electron.*, **1**, 12, Dec. 2018, pp. 622-635, doi: 10.1038/s41928-018-0173-2.
- [2] H.-J. Song, "Packages for Terahertz Electronics," *Proc. IEEE* **105**, 6, June 2017, pp.1121-1138, doi: 10.1109/JPROC.2016.2633547.
- [3] J. Champion *et al.*, "Toward industrial Exploitation of THz Frequencies: Integration of SiGe MMICs in silicon-micromachined waveguide systems," *IEEE Trans. Terahertz Science Tech.*, **9**, 6, Nov. 2019, pp. 624-636, doi: 10.1109/TTHZ.2019.2943572.
- [4] A. Krivovitca *et al.*, "Micromachined Silicon-Core Substrate-Integrated Waveguides at 220–330 GHz," *IEEE Trans. Microwave Theory Tech.*, **68**, 12, Dec. 2020, pp. 5123-5131, doi: 10.1109/TMTT.2020.3022060.
- [5] X. Yu *et al.*, "Efficient Mode Converter to Deep-Subwavelength Region with Photonic-crystal Waveguide Platform for Terahertz Applications," *Optics Express*, **27**, 20, Sept. 2019, pp. 28707-28721, doi: 10.1364/OE.27.028707.
- [6] D. Headland *et al.*, "Unclad Microphotronics for Terahertz Waveguides and Systems," *J. Lightwave Technology*, **38**, 24, Dec. 2020, pp. 6853-6862, doi: 10.1109/JLT.2020.3021681.